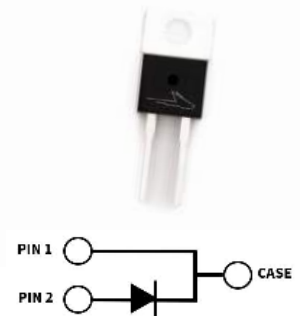


C4D15120A

4th Generation 1200 V, 15 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Package Types: TO-220-2
Marking: C4D15120A

Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior

Applications

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

Maximum Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V		
DC Blocking Voltage	V_{DC}	1200			
Continuous Forward Current	I_F	43.5	A	$T_J = 25^\circ\text{C}$	Fig. 3
		21		$T_J = 135^\circ\text{C}$	
		15		$T_J = 152.5^\circ\text{C}$	
Repetitive Peak Forward Surge Current	I_{FRM}	68	A	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$	Fig. 8
		44		$T_C = 110^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$	
Non-Repetitive Forward Surge Current	I_{FSM}	100	A	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$	Fig. 8
		85		$T_C = 110^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$	
Non-Repetitive Peak Forward Surge Current	$I_{F,Max}$	900	A	$T_C = 25^\circ\text{C}, t_p = 10\text{ }\mu\text{s}, \text{Pulse}$	
		750		$T_C = 110^\circ\text{C}, t_p = 10\text{ }\mu\text{s}, \text{Pulse}$	
Power Dissipation	P_{tot}	214	W	$T_J = 25^\circ\text{C}$	Fig. 4
		93		$T_J = 110^\circ\text{C}$	
i^2t Value	i^2t	50	A^2s	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$	
		36		$T_C = 110^\circ\text{C}, t_p = 10\text{ ms}$	

Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Notes
Forward Voltage	V_F	1.6	1.8	V	$I_F = 15 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	Fig. 1
		2.2	3		$I_F = 15 \text{ A}, T_j = 175 \text{ }^\circ\text{C}$	
Reverse Current	I_R	35	200	μA	$V_R = 1200 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$	Fig. 2
		120	300		$V_R = 1200 \text{ V}, T_j = 175 \text{ }^\circ\text{C}$	
Total Capacitive Charge	Q_C	77.5		nC	$V_R = 800 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$	Fig. 5
Total Capacitance	C	1200		pF	$V_R = 0 \text{ V}, T_j$	

Typical Performance

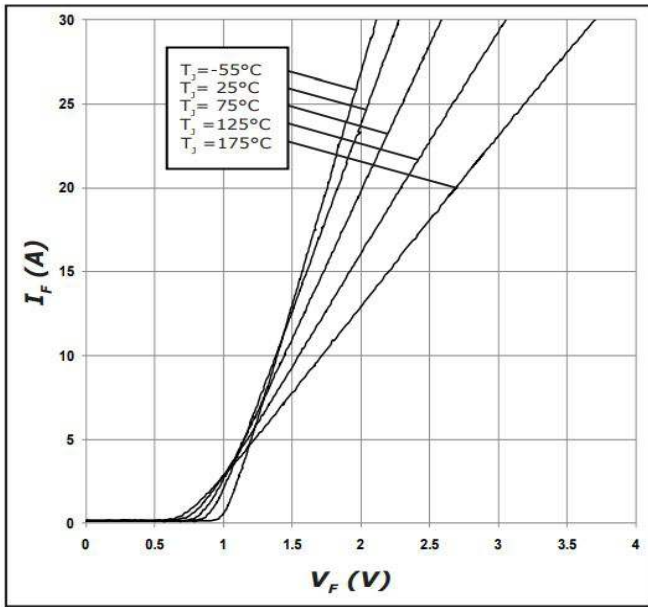


Figure 1
Forward Characteristics

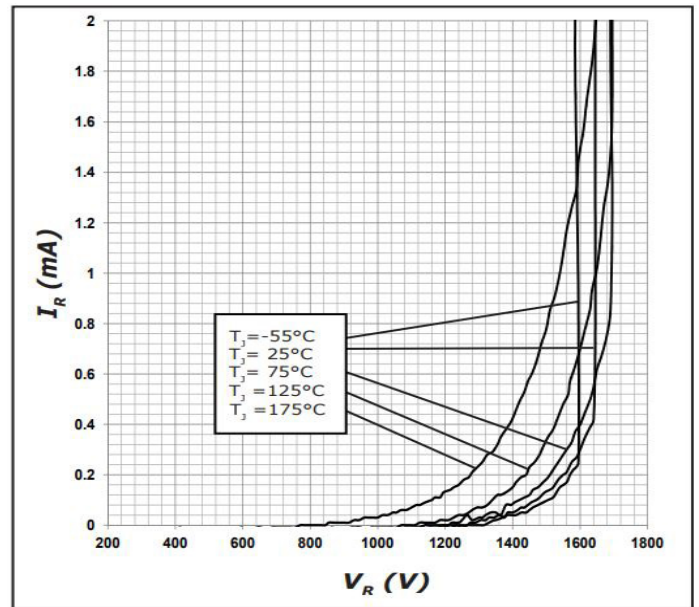


Figure 2
Reverse Characteristics

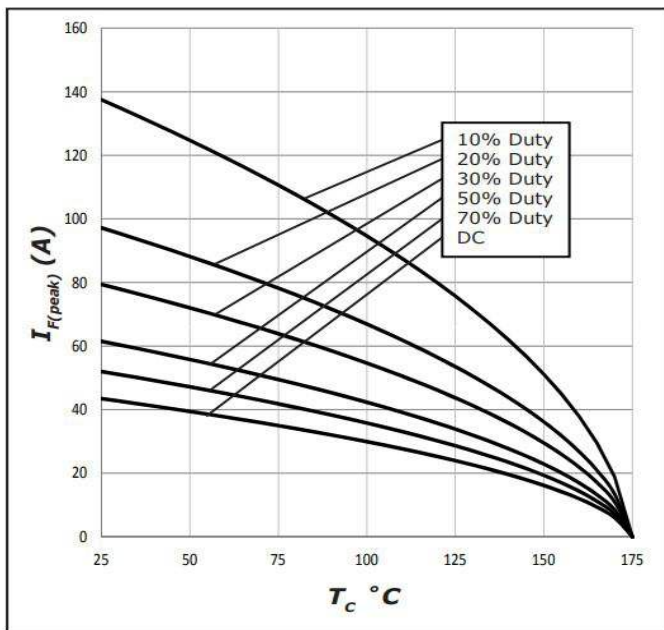


Figure 3
Current Derating

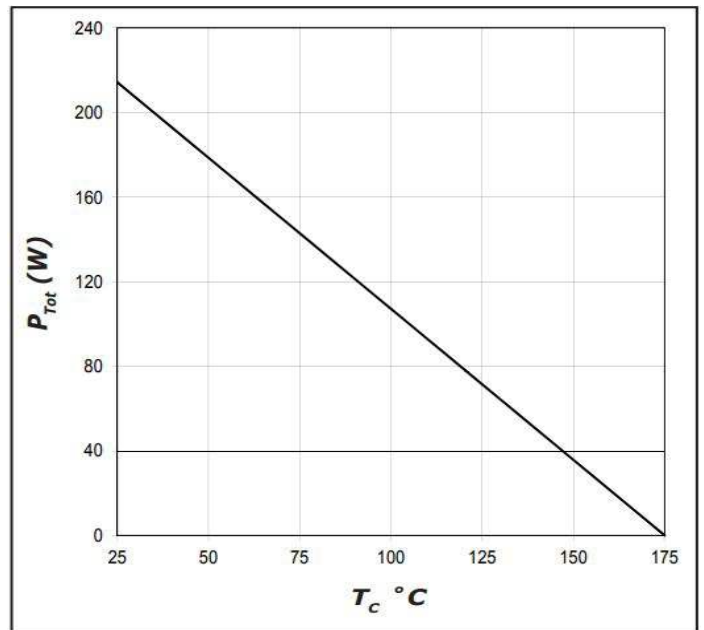


Figure 4
Power Derating

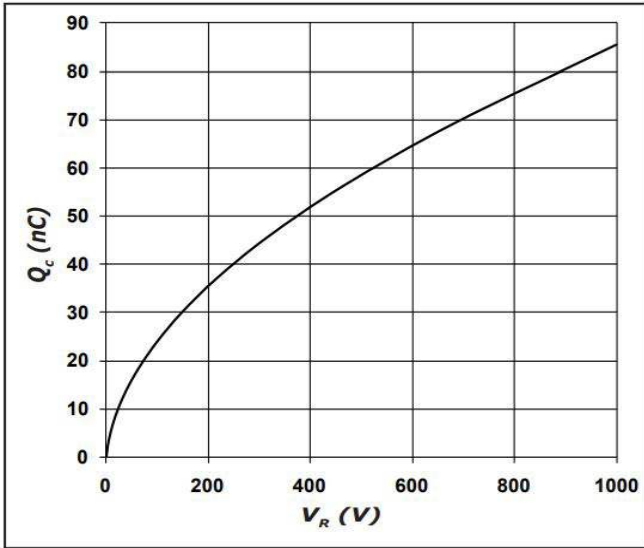


Figure 5

Total Capacitance vs. Reverse Voltage

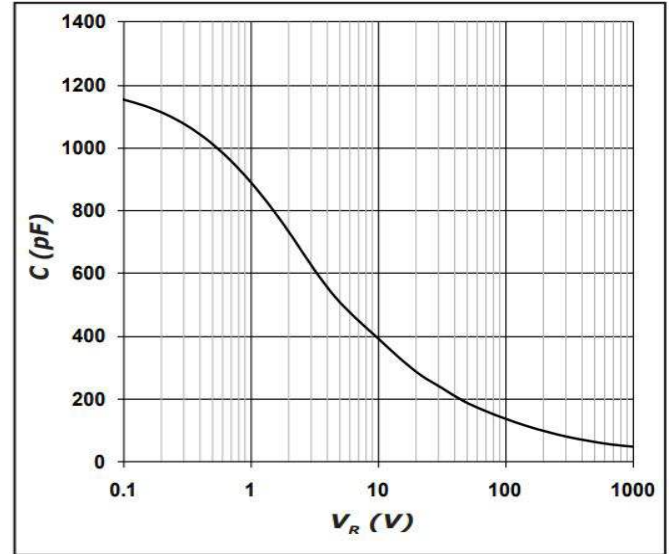


Figure 6

Capacitance vs. Reverse Voltage

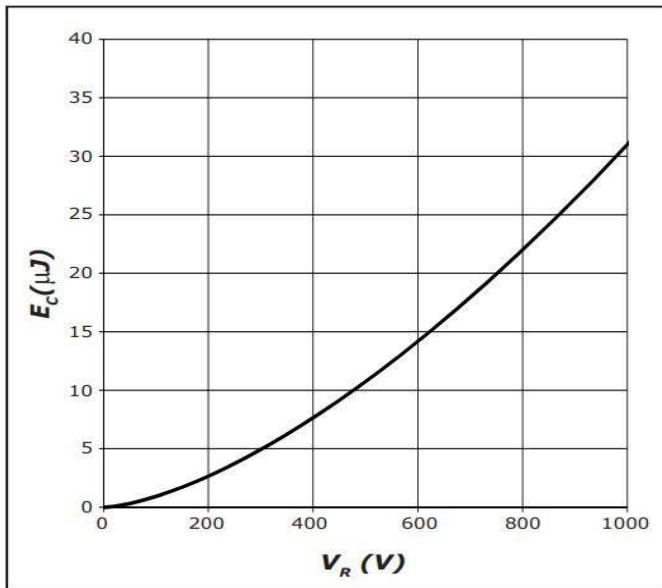


Figure 7

Capacitance Stored Energy

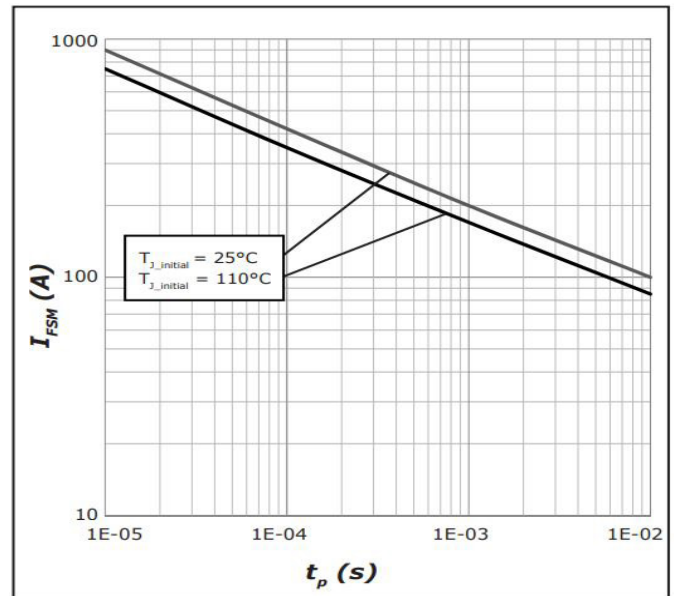


Figure 8

Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

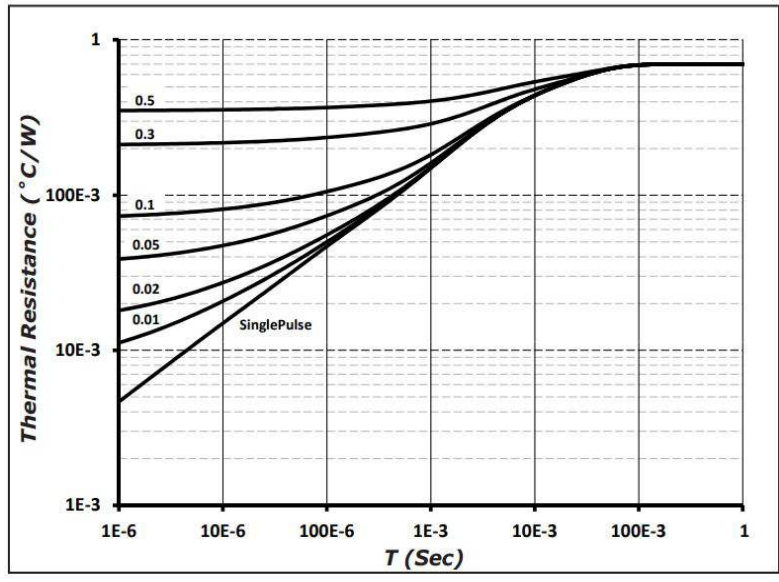
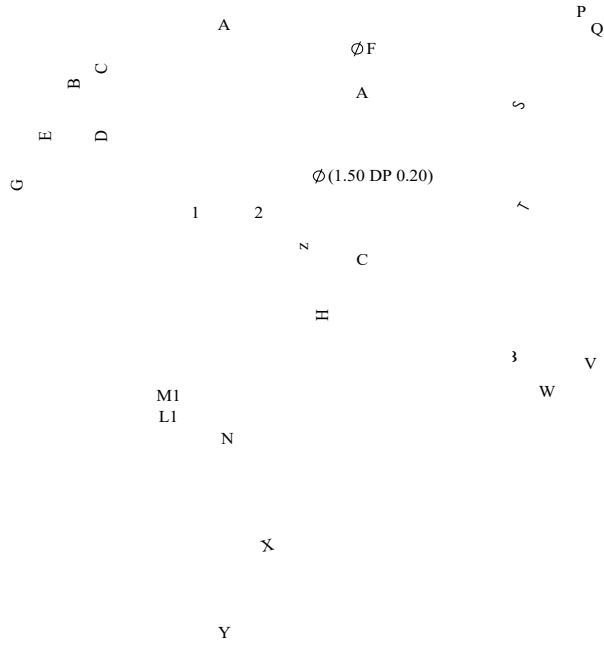


Figure 9
Transient Thermal Impedance



Package Dimensions & Pin-Out

Package: TO-220-2



NOTES

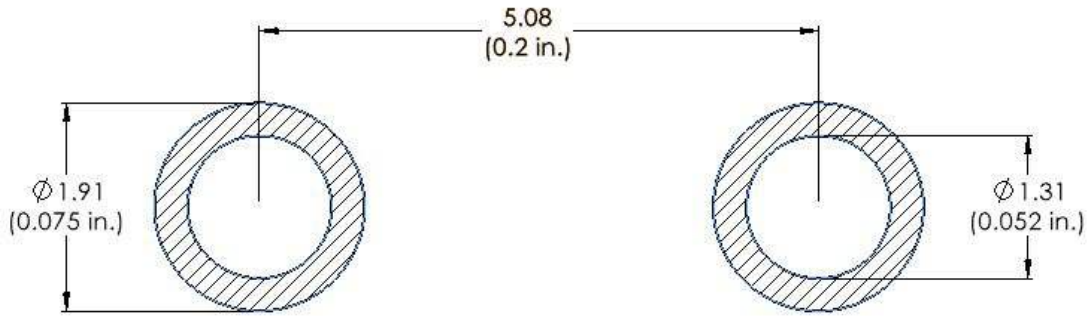
- 1. ALL METAL SURFACES SHALL BE FINISHED BY MEANS OF A PROPER METAL FINISHING PROCESS.
- 2. DIMENSIONS ARE IN MILLIMETERS UNLESS OTHERWISE SPECIFIED.
- 3. ALL DIMENSIONS ARE TOLERANCES UNLESS OTHERWISE SPECIFIED.
- 4. PACKAGE BURR IS NOT INCLUDED IN TOLERANCES.





Recommended Solder Pad Layout

Primary dimensions shown in mm.



Product Ordering Information

Order Number	Packing Type
C4D15120A	Tube



Revision History

Document Version	Date of Release	Description of Changes
1	October-2016	Initial Release
5	March-2023	Update Package Drawing Update Landing Pad



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